Alfa-MOS Technology

AFN1330S
60V N-Channel Enhancement Mode MOSFET

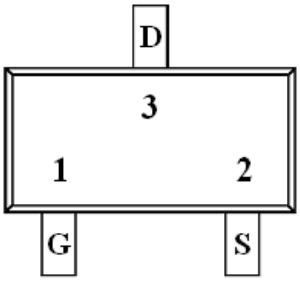
General Description

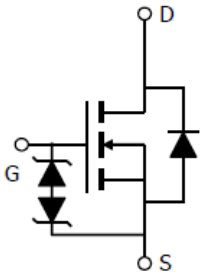
AFN1330S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.
These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

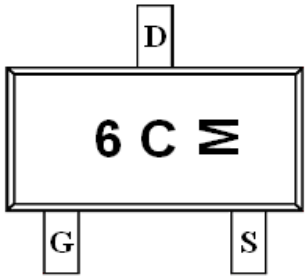
Features

- 60V/0.5A , $R_{DS(ON)}$=7.5Ω@V_{GS}=10V
- 60V/0.05A , $R_{DS(ON)}$=7.5Ω@V_{GS}=5V
- Super high density cell design for extremely low RDS (ON)
- Exceptional on-resistance and maximum DC current capability
- ESD Protection (1KV) Diode design–in
- SOT-323 package design

Pin Description (SOT-323)







Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- High saturation current capability. Direct Logic-Level Interface: TTL/CMOS
- Battery Operated Systems
- Solid-State Relays

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN1330SS32RG	6CM	SOT-323	Tape & Reel	3000 EA

※ 6C Parts code
※ M Month code
※ AFN1330SS32RG : 7” Tape & Reel ; Pb- Free ; Halogen- Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	0.115	A
	T_A=70℃		0.075	
Pulsed Drain Current		I_{DM}	0.8	A
Continuous Source Current(Diode Conduction)		I_S	0.115	A
Power Dissipation	T_A=25℃	P_D	225	mW
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	417	℃/W

Electrical Characteristics

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0	1.6	2.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			3	uA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V			1	uA
		V_{DS}=60V,V_{GS}=0V T_J=85℃			10	
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=0.5A		1.4	7.5	Ω
		V_{GS}= 5V,I_D=0.05A		1.8	7.5	
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=0.2A	80			mS
Diode Forward Voltage	V_{SD}	I_S=0.115A,V_{GS}=0V			1.5	V
Dynamic						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V f=1MHz		17	50	pF
Output Capacitance	C_{oss}			10	25	
Reverse Transfer Capacitance	C_{rss}			3	5	
Turn-On Time	$t_{d(on)}$	V_{DD}=25V,R_L=50Ω I_D≡0.5A,V_{GEN}=10V,R_G=25Ω		7	20	ns
Turn-Off Time	$t_{d(off)}$			11	40	

Typical Characteristics

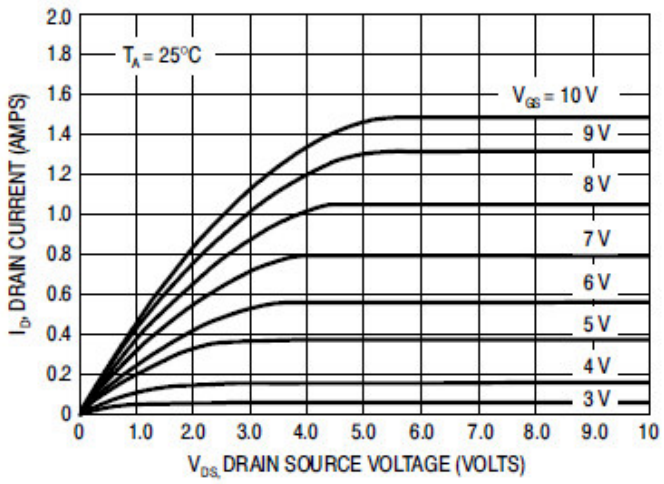


Figure 1. Ohmic Region

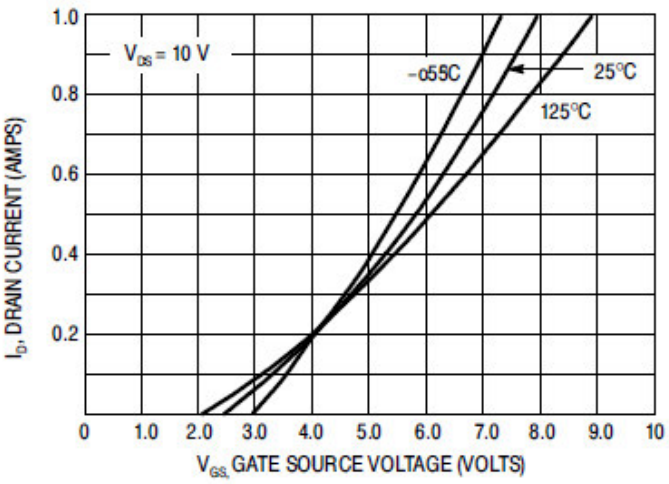


Figure 2. Transfer Characteristics

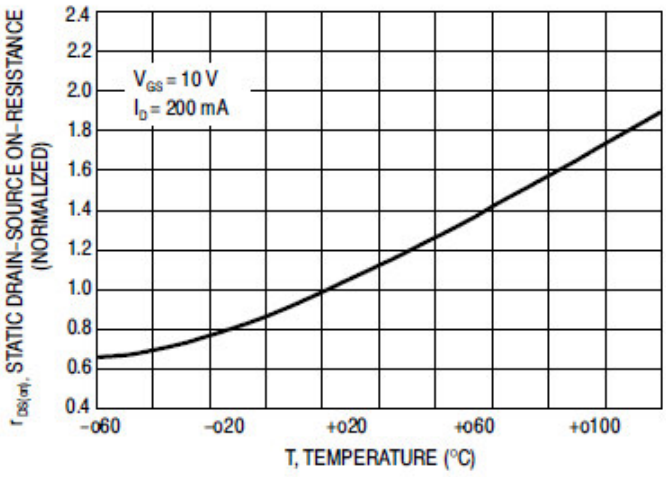


Figure 3. Temperature versus Static Drain–Source On–Resistance

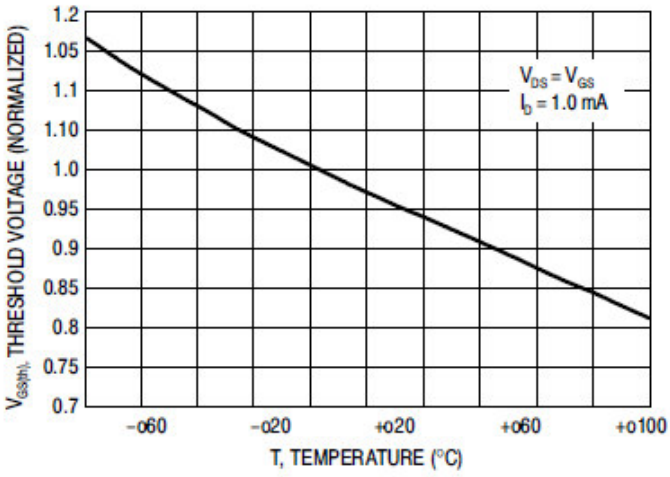
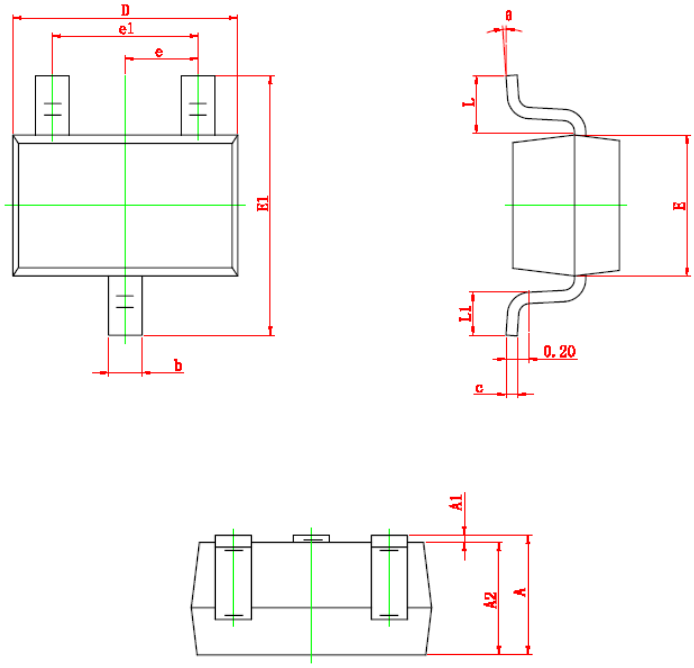


Figure 4. Temperature versus Gate Threshold Voltage

Package Information (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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